

ABSTRACT

An object of the present invention is to provide a low-resistance n-type Group III nitride semiconductor
5 layered structure having excellent flatness and few pits.

The inventive n-type group III nitride semiconductor layered structure comprises a substrate and, stacked on the substrate, an n-type impurity concentration periodic variation layer comprising an n-type impurity atom higher concentration layer and an n-type impurity atom lower concentration layer, said lower concentration layer being
10 stacked on said higher concentration layer.